

## Features

- 1、Leading edge sub micro trench technology with 750Mcell/in<sup>2</sup> (or higher) technology.
- 2、Low R<sub>DS(on)</sub> technology to minimize conductive losses.
- 3、Low leakage current.
- 4、High immunity to dynamic turn-on.

Part Number	Type	V <sub>DSS</sub>	V <sub>GSS</sub>	I <sub>D</sub>	V <sub>GS(th)</sub>	R <sub>DS(ON)</sub> (mΩ max) at V <sub>GS</sub> =					ESD	Package
		(V)	(±V)	(A)	Typ.(V)	10V	4.5V	4V	2.5V	1.8V	KV	
<b>◆ 12V Trench Power MOSFET</b>												
CM2311	P	-12	8	-3.5	-0.5		52		63	71		SOT-23
CM3447	P	-12	8	-4.5	-0.6		40		53	72		TSSOP-6
CM6465	P	-12	8	-8.8	-0.48		12		17	25		TSSOP-8
<b>◆ 20V Trench Power MOSFET</b>												
CM2300	N	20	12	5.4	0.78		30		40			SOT-23
CM2301	P	-20	12	-2.8	-0.65		100		150	170		SOT-23
CM2301E	P	-20	8	-2.8	-0.5		110		150		2	SOT-23
CM2302	N	20	8	2.8	0.8		60		115	130		SOT-23
CM2305	P	-20	12	-4.5	-0.85		52		70			SOT-23
CM2312	N	20	8	4.9	0.6		31		37	47		SOT-23
CM2314	N	20	8	5	0.55		25		30	40	2	SOT-23
CM2602	N	20	12	5.5	0.6	30	34		50			SOT-23-6L
CM3413	P	-20	8	3	0.65		80		100	130		SOT-23-6L
CM3414	N	20	8	4.2	0.6		50		63	87		SOT-23-6L
CM3415	P	-20	8	-4	-0.6		55		63	73	2	SOT-23-3L
CM3416	N	20	8	6.5	0.55		24		28	36	2	SOT-23-3L
CM3443	P	-20	12	-4.7	-0.85		60		100			SOT-23-6L
CM3814	Dual-N	20	10	6	0.7		17	19	24		2	DFN3×3
CM5853	P	-20	12	-3.5	-0.65		90		110	130		DFN3x2-8L
CM6463	P	-20	8	-6.2	-0.5		20		27	35		TSSOP-8
CM5N20V	Dual-N	20	12	6	0.67		30		40			SOT-23-6L
CM6968E	Dual-N	20	12	6.5	0.8		24	25	32		2	TSSOP-8
CM6968ES	Dual-N	20	12	6	0.8		24	25	32		2	SOT-23-6L
CM8205	Dual-N	20	12	6	0.67		30		40			SOT-23-6L
CM8205A	Dual-N	20	12	6	0.67		28		40			TSSOP-8
CM8804	Dual-N	20	12	8	0.67	13	14		19	27	2	TSSOP-8
CM8810	Dual-N	20	8	7	0.55		20		24	32	2	TSSOP-8
CM8820	Dual-N	20	12	6.5	0.8		24		32		2	TSSOP-8
CM8822	Dual-N	20	12	7	0.6	21	24		32	50		TSSOP-8
CM8822S	Dual-N	20	12	6	0.6	21	24		32	50		SOT-23-6L

Part Number	Type	V <sub>DSS</sub>	V <sub>GSS</sub>	I <sub>D</sub>	V <sub>GS(th)</sub>	R <sub>DS(ON)</sub> (mΩ max) at V <sub>GS</sub> =					ESD	Package
		(V)	(±V)	(A)	Typ.(V)	10V	4.5V	4V	2.5V	1.8V	KV	
<b>◆ 20V Trench Power MOSFET</b>												
CM9926	Dual-N	20	12	6	0.65		28		40			SOP-8
CM9926E	Dual-N	20	8	8	0.55		21		25	33	2	SOP-8
<b>◆ 30V Trench Power MOSFET</b>												
CM2306	N	30	20	4	1.5	37	49					SOT-23
CM2307	P	-30	20	-3.2	-1.4	70	95					SOT-23
CM2605	P	-30	20	-4.5	-1.4	60	90					SOT-23-6L
CM3018	N	30	20	0.1	1			8	13		0.5	SOT-323
CM3055	N	30	20	15	1.4	26	40					TO-252
CM3400	N	30	12	5.8	1.05	28	33		52			SOT-23-3L
CM3401	P	-30	12	-4.2	-1	60	75		120			SOT-23-3L
CM3401A	P	-30	12	-4	-1.1	50	60		85			SOT-23-3L
CM3404	N	30	20	5.8	1.5	28	43					SOT-23-3L
CM3407	P	-30	20	-4.3	-1.4	60	78					SOT-23-3L
CM3407A	P	-30	20	-4.3	-1.35	48	75					SOT-23-3L
CM3812	N	30	20	2	1.5	42	125		200			DFN3x3
CM4404	N	30	12	8.5	0.9	24	30		48			SOP-8
CM4407	P	-30	25	-10	-1.8	20	28					SOP-8
CM4409	P	-30	20	-15	-1.9	7.5	12					Sop-8
CM4410	N	30	20	10	1.9	15	24					SOP-8
CM4411DY	P	-30	20	-13	-1.3	11	16					SOP-8
CM4414	N	30	20	8.5	1.5	26	40					SOP-8
CM4422	N	30	20	11	1.9	15	24					SOP-8
CM4430	N	30	20	18	1.7	6	10					SOP-8
CM4435	P	-30	20	-9.1	-1.4	20	35					SOP-8
CM4444	N	30	20	20	1.7	5.5	7					SOP-8
CM4604	N+P	30	20	6.9	1.5	26	40					SOP-8
		-30	20	-5	-1.4	60	90					
CM4606	N+P	30	20	6.9	1.5	26	40					SOP-8
		-30	20	-6	-1.35	42	70					
CM4800	Dual-N	30	12	6.9	0.9	27	32		50			SOP-8
CM4812	Dual-N	30	20	6.9	1.5	26	40					SOP-8
CM4953	Dual-P	-30	20	-5.3	-1.4	60	90					SOP-8
CM4953A	Dual-P	-30	20	-5.7	-1.35	42	70					SOP-8
CM55N03	N	25	20	55	1.9	6	9					TO-252

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		(V)	(±V)	(A)	Typ.(V)	10V	4.5V	4V	2.5V	1.8V	KV	
<b>◆ 30V Trench Power MOSFET</b>												
CM6680	N	30	20	12	1.9	11	15					SOP-8
CM8831	Dual-P	-30	20	-9.1	-1.4	21	35					SOP-8
CM8958	N+P	30	20	6.5	1.5	28	42					SOP-8
		-30	20	-5.3	-1.4	60	90					
CM9435	P	-30	20	-5.3	-1.4	60	90					SOP-8
CM9435A	P	-30	20	-5.7	-1.35	42	70					SOP-8
<b>◆ 40V Trench Power MOSFET</b>												
CM1404	N	40	20	162	3	4						TO-220
CM2504	N	40	20	18	1.9	25	45					TO-252
CM4404	P	-40	20	-15	-2	44	68					TO-252
CM4565	N+P	40	12	3.9	1.12	40	54					SOP-8
		-40	16	-3.3	-1	54	72					
CM4614	N+P	40	20	6	1.8	31	45					SOP-8
		-40	20	-5	-1.9	45	63					
CM4942	Dual-N	40	20	5.3	1.8	21	28					SOP-8
<b>◆ 60V Trench Power MOSFET</b>												
CM1010	N	60	20	84	3	12						TO-220
CM25N06	N	60	20	15	1.8	41						TO-252
CM3205	N	55	20	110	3	18						TO-220
CM3206	N	60	20	210	3	3						TO-220
CM4436	N	60	20	7.1	1.8	33	40					SOP-8
CM4440	N	60	20	5	1.5	55	75					SOP-8
CM4946	Dual-N	60	20	5.3	1.5	41	52					SOP-8
CM60N06	N	60	20	60	3	16						TO-220
CMFZ40	N	60	20	49	2.8	18						TO-220
CM2N7002	N	60	20	0.12	1.6	7500	7500					SOT-23
CM2N7002K	N	60	20	0.4	1.6	3000	4000				2	SOT-23
CM2N7002W	N	60	20	0.12	1.6	7500	7500					SOT-323
CM2N7002KW	N	60	20	0.32	1.6	2300	2700				2	SOT-323
CM2N7002KM	N	60	20	0.12	1.85	7500	7500				2	SOT-723
<b>◆ 70V( or higher) Power MOSFET</b>												
CM15N75	N	75	20	15	2.5	96	105				2	TO-252
CM16P10	P	-100	20	-11	-2.5	195	210					TO-252
CM10N10	N	100	20	17	1.8	70						TO-252

Part Number	Type	V <sub>DSS</sub>	V <sub>GSS</sub>	I <sub>D</sub>	V <sub>GS(th)</sub>	R <sub>DS(ON)</sub> (mΩ max) at V <sub>GS</sub> =					ESD	Package
		(V)	(±V)	(A)	Typ.(V)	10V	4.5V	4V	2.5V	1.8V	KV	
<b>◆70V( or higher) Power MOSFET</b>												
CM19N10	N	100	25	15	3	100						TO-252
CM3207	N	75	20	180	3	4.5						TO-220
CM4110	N	100	20	180	3	4.5						TO-220
CM4310	N	100	20	140	3	7						TO-220
CM4460	N	100	20	3.6	2.5	120	145					
CM45N10	N	100	25	42	2.5	54						TO-220
CM4610	N	100	20	73	3	14						TO-220
CM4950	N	100	20	3.3	2.5	115	137					
CM4952	N	100	20	1.8	2.5	270	300		350			SOP-8
CM75N06	N	70	20	60	3	16						TO-220
CM75N75	N	75	20	80	3	11						TO-220
CM75N80	N	80	20	110	3	11						TO-220
CM80N75	N	75	25	93	3	10						TO-220
CM95N10	N	100	25	120	3	9						TO-220

**MOSFET 选型:**

- A、了解客户的应用场合,针对寻找pin-to-pin的替代方案;
- B、查找被替代的Mofset的相关参数,如:封装, Id, Vds, Vgs, Rds(on) 等相关参数;
- C、利用Excel的筛选功能Selection Guide里查找参数相近或优于被替代组件的参数;
- D、利用cross reference文档直接对该需替代料号进行替代。

**Note:** 对于同步整流的电源架构,特别是输入电压与输出电压差别较大的应用里,要求High side Mosfet的

输入电容较小,而low side Mosfet的Rds(on)较小。

**MOSFET的选择:**

针对全新设计的方案应尽量了解客户的应用场合,得到应用的具体参数,如:

驱动信号的电压?电流和工作频率?

输入电压和输出电压,负载电流的大小。

信号的工作方式?对于效率是否有要求?

对空间有何需求,其他特殊需求...